

# Rochester Electronics Manufactured Components

Rochester branded components are manufactured using either die/wafers purchased from the original suppliers or Rochester wafers recreated from the original IP. All recreations are done with the approval of the OCM.

Parts are tested using original factory test programs or Rochester developed test solutions to guarantee product meets or exceed the OCM data sheet.

### **Quality Overview**

- ISO-9001
- AS9120 certification
- Qualified Manufacturers List (QML) MIL-PRF-35835
  - Class Q Military
  - Class V Space Level
- Qualified Suppliers List of Distributors (QSLD)
- Rochester is a critical supplier to DLA and meets all industry and DLA standards.

Rochester Electronics, LLC is committed to supplying products that satisfy customer expectations for quality and are equal to those originally supplied by industry manufacturers.

The original manufacturer's datasheet accompanying this document reflects the performance and specifications of the Rochester manufactured version of this device. Rochester Electronics guarantees the performance of its semiconductor products to the original OEM specifications. 'Typical' values are for reference purposes only. Certain minimum or maximum ratings may be based on product characterization, design, simulation, or sample testing.

Preferred Device

## **Amplifier Transistors**

### **PNP Silicon**

#### **Features**

• Pb-Free Packages are Available\*

### **MAXIMUM RATINGS**

Rating	Symbol	2N5400	2N5401	Unit
Collector – Emitter Voltage	V <sub>CEO</sub>	120 150		Vdc
Collector – Base Voltage	V <sub>CBO</sub>	130	160	Vdc
Emitter – Base Voltage	V <sub>EBO</sub>	5.0		Vdc
Collector Current – Continuous	I <sub>C</sub>	600		mAdc
Total Device Dissipation  @ T <sub>A</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	625 5.0		mW mW/°C
Total Device Dissipation  @ T <sub>C</sub> = 25°C  Derate above 25°C	P <sub>D</sub>	1.5 12		Watts mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150		°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

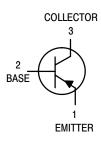
### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	°C/W



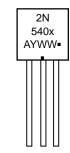
### ON Semiconductor®

### http://onsemi.com





### **MARKING DIAGRAM**



A = Assembly Location

Y = Year WW = Work Week ■ = Pb-Free Package

(Note: Microdot may be in either location)

### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

**Preferred** devices are recommended choices for future use and best overall value.

### **ELECTRICAL CHARACTERISTICS** (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage <sup>(1)</sup> (I <sub>C</sub> = 1.0 mAdc, I <sub>B</sub> = 0)	2N5400 2N5401	V <sub>(BR)</sub> CEO	120 150	_ _	Vdc
Collector–Base Breakdown Voltage ( $I_C = 100 \mu Adc, I_E = 0$ )	2N5400 2N5401	V <sub>(BR)CBO</sub>	130 160	_ _	Vdc
Emitter-Base Breakdown Voltage $(I_E = 10 \mu Adc, I_C = 0)$		V <sub>(BR)EBO</sub>	5.0	_	Vdc
Collector Cutoff Current $(V_{CB} = 100 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 100 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$ $(V_{CB} = 120 \text{ Vdc}, I_E = 0, T_A = 100^{\circ}\text{C})$	2N5400 2N5401 2N5400 2N5401	Ісво	- - -	100 50 100 50	nAdc μAdc
Emitter Cutoff Current (V <sub>EB</sub> = 3.0 Vdc, I <sub>C</sub> = 0)		I <sub>EBO</sub>	-	50	nAdc
ON CHARACTERISTICS (Note 1)				•	•
DC Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)	2N5400 2N5401	h <sub>FE</sub>	30 50	_ _	_
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5400 2N5401		40 60	180 240	
$(I_C = 50 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$	2N5400 2N5401		40 50	_ _	
Collector–Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )		V <sub>CE(sat)</sub>	- -	0.2 0.5	Vdc
Base-Emitter Saturation Voltage ( $I_C = 10 \text{ mAdc}$ , $I_B = 1.0 \text{ mAdc}$ ) ( $I_C = 50 \text{ mAdc}$ , $I_B = 5.0 \text{ mAdc}$ )		V <sub>BE(sat)</sub>	_ _	1.0 1.0	Vdc
SMALL-SIGNAL CHARACTERISTICS		·			
Current-Gain — Bandwidth Product $(I_C = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 100 \text{ MHz})$	2N5400 2N5401	f <sub>T</sub>	100 100	400 300	MHz
Output Capacitance (V <sub>CB</sub> = 10 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>obo</sub>	-	6.0	pF
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 10 Vdc, f = 1.0 kHz)	2N5400 2N5401	h <sub>fe</sub>	30 40	200 200	_
Noise Figure (I <sub>C</sub> = 250 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 $k\Omega$ , f = 1.0 kHz)		NF	-	8.0	dB

Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.

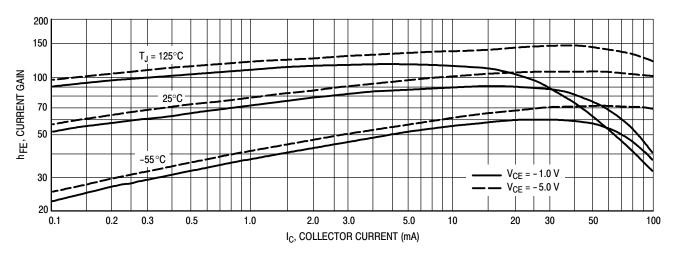


Figure 1. DC Current Gain

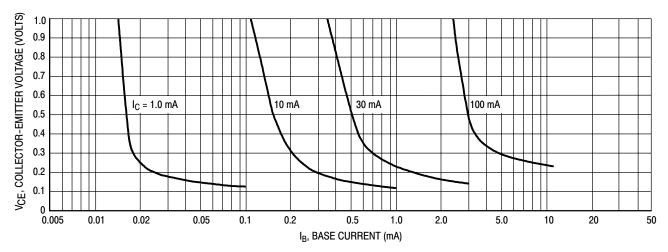


Figure 2. Collector Saturation Region

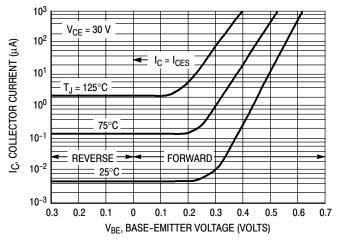


Figure 3. Collector Cut-Off Region

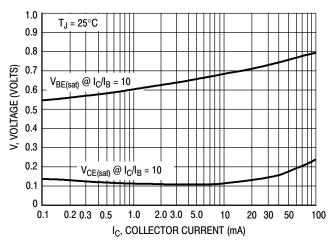


Figure 4. "On" Voltages

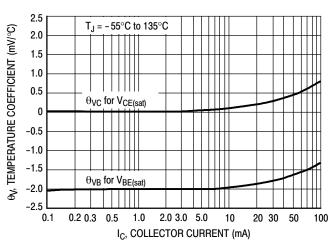
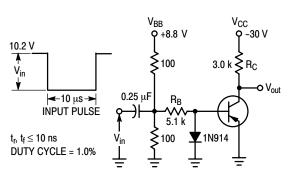


Figure 5. Temperature Coefficients



Values Shown are for I<sub>C</sub> @ 10 mA

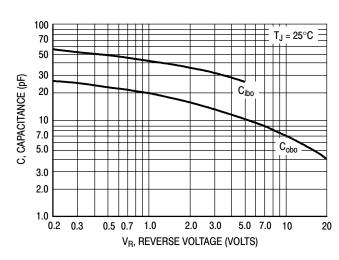
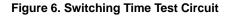


Figure 7. Capacitances



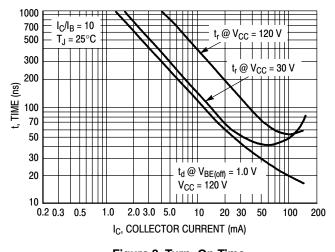


Figure 8. Turn-On Time

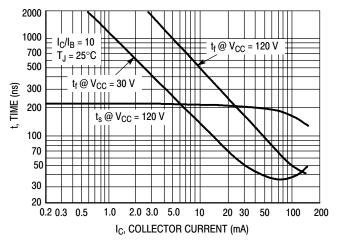


Figure 9. Turn-Off Time

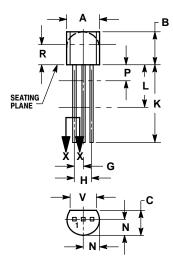
### **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>	
2N5400	TO-92	5000 Unit / Bulk	
2N5400G	TO-92 (Pb-Free)	5000 Unit / Bulk	
2N5400RLRP	TO-92	2000 Tape & Reel	
2N5400RLRPG	TO-92 (Pb-Free)	2000 Tape & Reel	
2N5401	TO-92	5000 Unit / Bulk	
2N5401G	TO-92 (Pb-Free)	5000 Unit / Bulk	
2N5401RL1	TO-92	2000 Tape & Reel	
2N5401RL1G	TO-92 (Pb-Free)	2000 Tape & Reel	
2N5401RLRA	TO-92	2000 Tape & Reel	
2N5401RLRAG	TO-92 (Pb-Free)	2000 Tape & Reel	
2N5401RLRM	TO-92	2000 Tape & Ammo Box	
2N5401RLRMG	TO-92 (Pb-Free)	2000 Tape & Ammo Box	
2N5401ZL1	TO-92	2000 Tape & Ammo Box	
2N5401ZL1G	TO-92 (Pb-Free)	2000 Tape & Ammo Box	

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

TO-92 CASE 29-11 **ISSUE AL** 





- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
  CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
  LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
С	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250		6.35	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	

STYLE 1:

PIN 1. EMITTER

BASE COLLECTOR

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